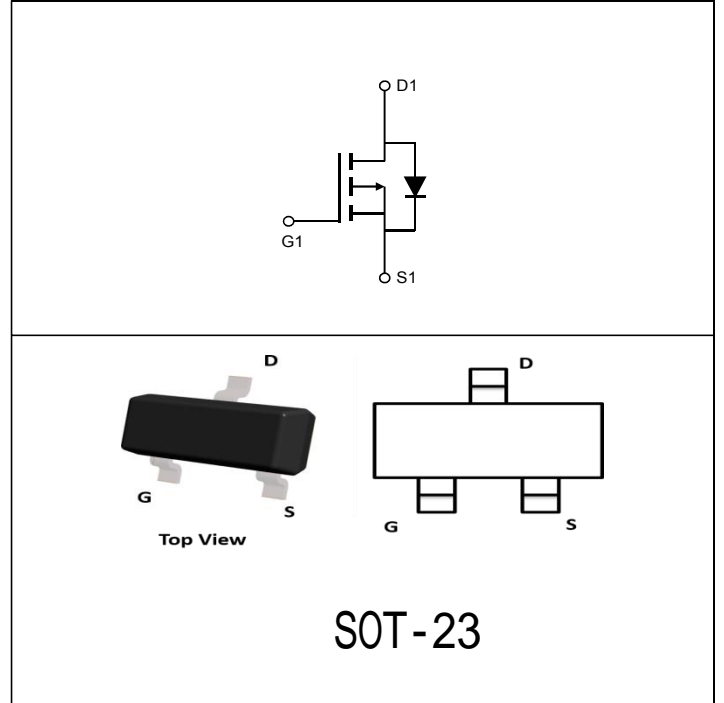


P-channel Enhancement Mode Mosfet

CX20P02A

DESCRIPTION

- -20V, -12A
 $R_{DS(ON)} < 21m\Omega @ V_{GS} = 4.5V$
 $R_{DS(ON)} < 28m\Omega @ V_{GS} = 2.5V$
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired



GENERAL FEATURES

- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Application

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Maximum	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	± 12	V
Drain Current	$T_A=25^\circ C$ Steady State	I_D	-12	A
	$T_A=70^\circ C$ Steady State		-7.8	
Pulsed Drain Current ^A		I_{DM}	-30	A
Total Power Dissipation @ $T_A=25^\circ C$ Steady State		P_D	1.5	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B		$R_{\theta JA}$	65	$^\circ C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$